

### VS-16TTS...FPPbF Series, VS-16TTS...FP-M3 Series

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## **High Voltage Phase Control Thyristor, 16 A**



ı	U-220 <i>F</i>	IB F	JLL-F	'AN

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Y	٦
0	9
1 (K)	(G) 3

PRODUCT SUMMARY					
Package	TO-220AB FP				
Diode variation	Single SCR				
I <sub>T(AV)</sub>	10 A				
$V_{DRM}/V_{RRM}$	800 V, 1200 V				
$V_{TM}$	1.4 V				
I <sub>GT</sub>	60 mA				
$T_J$	- 40 °C to 125 °C				

#### **FEATURES**

- · Designed and qualified for industrial level
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 approved
- 125 °C max. operating junction temperature
- Material categorization:
   For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





ROHS COMPLIANT HALOGEN

#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

### **DESCRIPTION**

The VS-16TTS..FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	13.5	17	А					

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I <sub>T(AV)</sub>	Sinusoidal waveform	10	Δ.			
I <sub>RMS</sub>		16	A			
V <sub>DRM</sub> /V <sub>RRM</sub>		800/1200	V			
I <sub>TSM</sub>		200	А			
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
TJ	Range	- 40 to 125	°C			

VOLTAGE RATINGS							
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA				
VS-16TTS08FPPbF, VS-16TTS08FP-M3	800	800	10				
VS-16TTS12FPPbF, VS-16TTS12FP-M3	1200	1200	10				



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	
PANAMETEN					MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 70 °C,	180° conduction, half sine wave	10		
Maximum RMS on-state current	I <sub>RMS</sub>			1	6	Α
Maximum peak, one-cycle,	1	10 ms sine p	oulse, rated V <sub>RRM</sub> applied	1	70	_ A
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine p	oulse, no voltage reapplied	2	00	
Marriage and 124 four fracing a	l <sup>2</sup> t	10 ms sine p	oulse, rated V <sub>RRM</sub> applied	1-	44	A <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200		A <sup>2</sup> S
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied		000	A²√s
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25 °C		1	.4	٧
On-state slope resistance	r <sub>t</sub>	T 405 00		24	4.0	mΩ
Threshold voltage	V <sub>T(TO)</sub>	$T_{\rm J} = 125  ^{\circ}{\rm C}$		1	.1	V
Maximum various and divast lackage current	1 /1	T <sub>J</sub> = 25 °C	V Peted V A/	0	.5	
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$V_R = Rated V_{RRM}/V_{DRM}$		1	0	
Holding current	l <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A 16TTS08FP, 16TTS12FP, $T_J$ = 25 °C		150	mA	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C 200		00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \max$	linear to 80 %, V <sub>DRM</sub> = R <sub>g</sub> - k = Open	5	00	V/µs
Maximum rate of rise of turned-on current	dI/dt			1	50	A/µs

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	$P_{GM}$		8.0	w		
Maximum average gate power	P <sub>G(AV)</sub>		2.0	7 **		
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α		
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V		
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	90			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60	mA		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35			
	V <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	3.0	V		
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0			
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	]		
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 125 °C V = Peted value	0.25			
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA		

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9				
Typical reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	4	μs			
Typical turn-off time	tq	1) = 125 0	110				

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C	
Maximum thermal resistance, junction to case		$R_{thJC}$	DC operation	2.5		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W	
Typical thermal resistance, case to heatsink		$R_{\text{thCS}}$	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	OZ.	
Mounting torque -	minimum			6 (5)	kgf · cm	
	maximum			12 (10)	(lbf · in)	
Madiandaria			0 TO 000 AD FULL DAY (0.44/0)	16TTS08FP		
Marking device			Case style TO-220AB FULL-PAK (94/V0)		16TTS12FP	

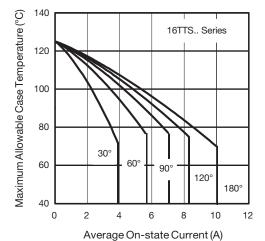


Fig. 1 - Current Rating Characteristics

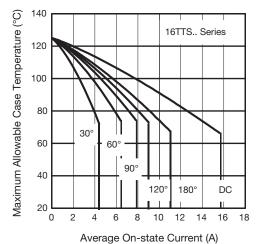


Fig. 2 - Current Rating Characteristics

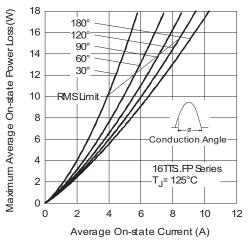


Fig. 3 - On-State Power Loss Characteristics

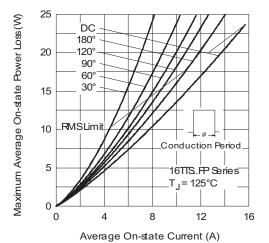


Fig. 4 - On-State Power Loss Characteristics

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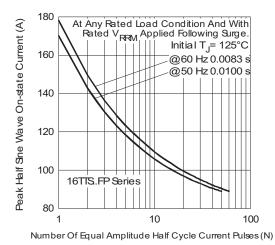


Fig. 5 - Maximum Non-Repetitive Surge Current

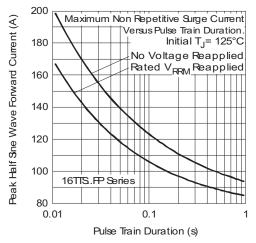


Fig. 6 - Maximum Non-Repetitive Surge Current



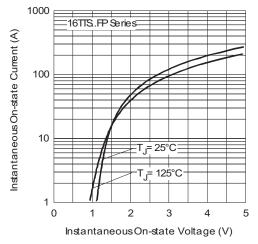


Fig. 7 - On-State Voltage Drop Characteristics

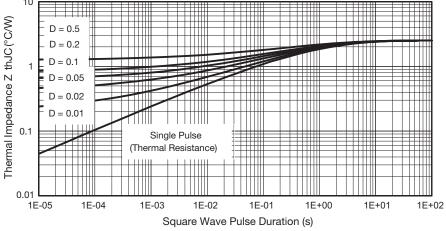
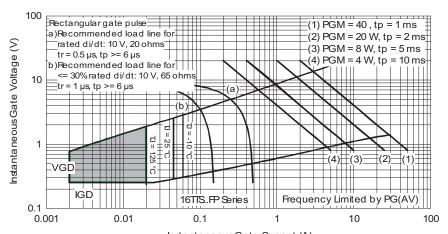


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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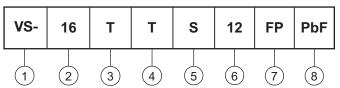
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Instantaneous Gate Current (A)
Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating, RMS value

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

7 - FULL-PAK

8 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

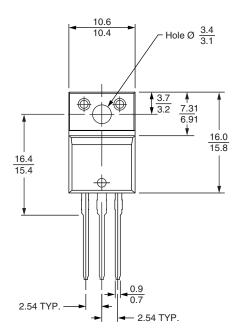
ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-16TTS08FPPbF	50	1000	Antistatic plastic tubes					
VS-16TTS08FP-M3	50	1000	Antistatic plastic tubes					
VS-16TTS12FPPbF	50	1000	Antistatic plastic tubes					
VS-16TTS12FP-M3	50	1000	Antistatic plastic tubes					

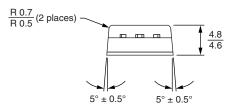
LINKS TO RELATED DOCUMENTS						
Dimensions		www.vishay.com/doc?95072				
Dort marking information	TO-220FP PbF	www.vishay.com/doc?95069				
Part marking information	TO-220FP -M3	www.vishay.com/doc?95456				

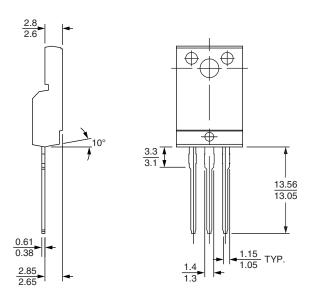


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### **DIMENSIONS** in millimeters







### Lead assignments

#### **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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